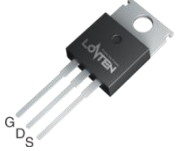
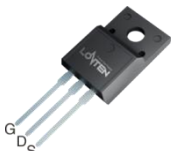

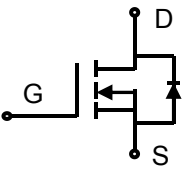



Lonten N-channel 800V, 4A Power MOSFET

<p>Description The Power MOSFET is fabricated using the advanced planer VDMOS technology. The resulting device has low conduction resistance, superior switching performance and high avalanche energy.</p> <p>Features</p> <ul style="list-style-type: none"> ◆ Low $R_{DS(on)}$ ◆ Low gate charge (typ. $Q_g = 18.9$ nC) ◆ 100% UIS tested ◆ RoHS compliant <p>Applications</p> <ul style="list-style-type: none"> ◆ Power factor correction. ◆ Switched mode power supplies. ◆ LED driver. 	<p>Product Summary</p> <table> <tr> <td>V_{DSS}</td> <td>800V</td> </tr> <tr> <td>I_D</td> <td>4A</td> </tr> <tr> <td>$R_{DS(on),max}$</td> <td>3.8Ω</td> </tr> <tr> <td>$Q_{g,typ}$</td> <td>18.9 nC</td> </tr> </table> <div style="display: flex; justify-content: space-around; align-items: center;"> <div style="text-align: center;">  <p>TO-220</p> </div> <div style="text-align: center;">  <p>TO-220F</p> </div> <div style="text-align: center;">  <p>TO-247</p> </div> </div> <div style="text-align: center; margin-top: 20px;">  <p>N-Channel MOSFET</p> </div> <div style="text-align: right; margin-top: 10px;">  </div>	V_{DSS}	800V	I_D	4A	$R_{DS(on),max}$	3.8 Ω	$Q_{g,typ}$	18.9 nC
V_{DSS}	800V								
I_D	4A								
$R_{DS(on),max}$	3.8 Ω								
$Q_{g,typ}$	18.9 nC								

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	800	V
Continuous drain current ($T_C = 25^\circ\text{C}$)	I_D	4	A
($T_C = 100^\circ\text{C}$)		2.5	A
Pulsed drain current ¹⁾	I_{DM}	16	A
Gate-Source voltage	V_{GSS}	± 30	V
Avalanche energy, single pulse ²⁾	E_{AS}	125	mJ
Peak diode recovery dv/dt ³⁾	dv/dt	5	V/ns
Power Dissipation TO-220F ($T_C = 25^\circ\text{C}$)	P_D	35	W
Derate above 25°C		0.28	W/ $^\circ\text{C}$
Power Dissipation TO-247/TO-220 ($T_C = 25^\circ\text{C}$)		95	W
Derate above 25°C		0.76	W/ $^\circ\text{C}$
Operating junction and storage temperature range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$
Continuous diode forward current	I_S	4	A
Diode pulse current	$I_{S,pulse}$	16	A

Thermal Characteristics

Parameter	Symbol	Value		Unit
		TO-220F	TO-247/TO-220	
Thermal resistance, Junction-to-case	$R_{\theta JC}$	3.57	1.32	$^\circ\text{C}/\text{W}$
Thermal resistance, Junction-to-ambient	$R_{\theta JA}$	62.5	62	$^\circ\text{C}/\text{W}$

Package Marking and Ordering Information

Device	Device Package	Marking	Units/Tube	Units/Reel
LNB4N80	TO-247	LNB4N80	30	
LND4N80	TO-220F	LND4N80	50	
LNC4N80	TO-220	LNC4N80	50	

Electrical Characteristics $T_c = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{GS}=0\text{ V}, I_D=0.25\text{ mA}$	800	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=0.25\text{ mA}$	2	-	4	V
Drain cut-off current	I_{DSS}	$V_{DS}=800\text{ V}, V_{GS}=0\text{ V},$ $T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	-	-	1 10	μA
Gate leakage current, Forward	I_{GSSF}	$V_{GS}=30\text{ V}, V_{DS}=0\text{ V}$	-	-	100	nA
Gate leakage current, Reverse	I_{GSSR}	$V_{GS}=-30\text{ V}, V_{DS}=0\text{ V}$	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=2\text{ A}$	-	3.4	3.8	Ω
Dynamic characteristics						
Input capacitance	C_{iss}	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$	-	499	-	pF
Output capacitance	C_{oss}		-	57.4	-	
Reverse transfer capacitance	C_{rss}		-	6.8	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 400\text{ V}, I_D = 4\text{ A}$ $R_G = 10\ \Omega, V_{GS}=15\text{ V}$	-	10.6	-	ns
Rise time	t_r		-	26	-	
Turn-off delay time	$t_{d(off)}$		-	46	-	
Fall time	t_f		-	32	-	
Gate charge characteristics						
Gate to source charge	Q_{gs}	$V_{DD}=640\text{ V}, I_D=4\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	3.96	-	nC
Gate to drain charge	Q_{gd}		-	10.5	-	
Gate charge total	Q_g		-	21.2	-	
Gate plateau voltage	$V_{plateau}$		-	4.3	-	V
Reverse diode characteristics						
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=4\text{ A}$	-	-	1.5	V
Reverse recovery time	t_{rr}	$V_R=400\text{ V}, I_F=4\text{ A}$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	380	-	ns
Reverse recovery charge	Q_{rr}		-	1.6	-	μC
Peak reverse recovery current	I_{rrm}		-	8.4	-	A

Notes:

- Pulse width limited by maximum junction temperature.
- $L=10\text{mH}, I_{AS}=5\text{A}$, Starting $T_j=25^\circ\text{C}$.
- $I_{SD}=4\text{A}, di/dt \leq 100\text{A}/\mu\text{s}, V_{DD} \leq BV_{DS}$, Starting $T_j=25^\circ\text{C}$.

Electrical Characteristics Diagrams

Figure 1. Typical Output Characteristics

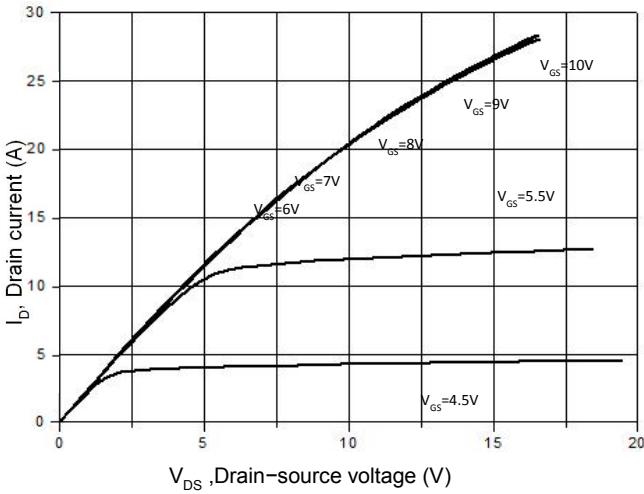


Figure 3. On-Resistance Variation vs. Drain Current

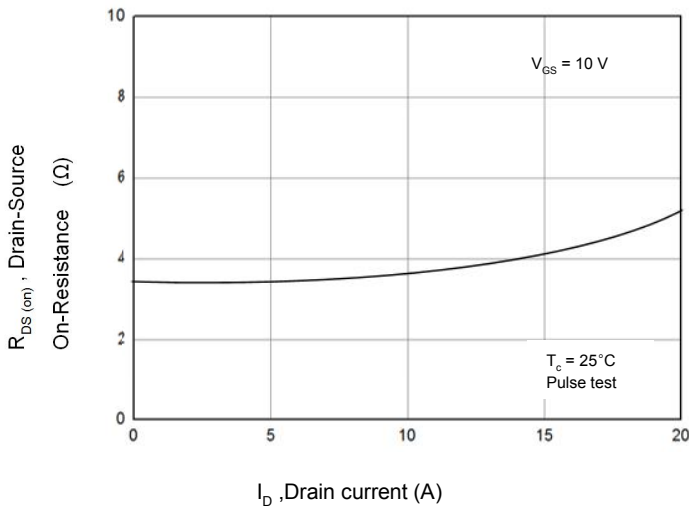


Figure 5. Breakdown Voltage vs. Temperature

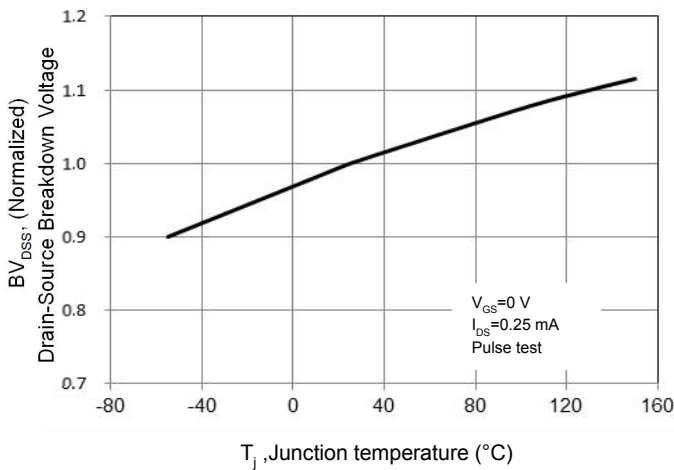


Figure 2. Transfer Characteristics

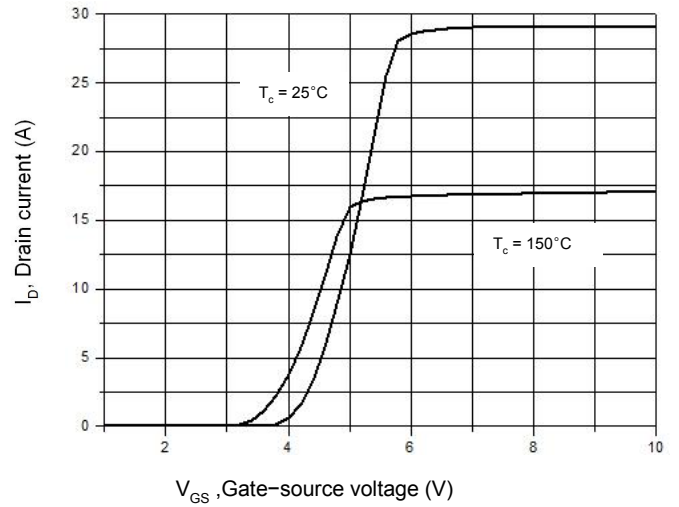


Figure 4. Threshold Voltage vs. Temperature

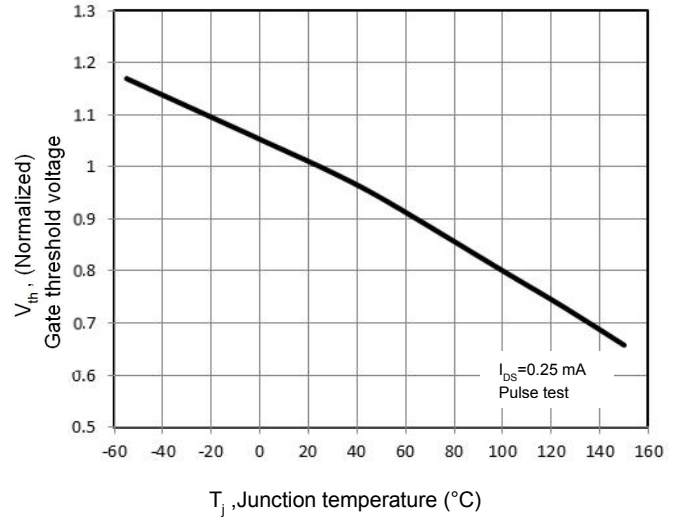


Figure 6. On-Resistance vs. Temperature

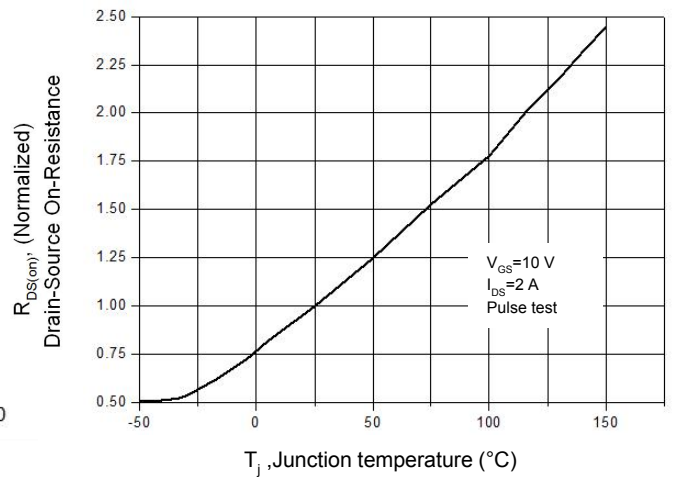


Figure 7. Capacitance Characteristics

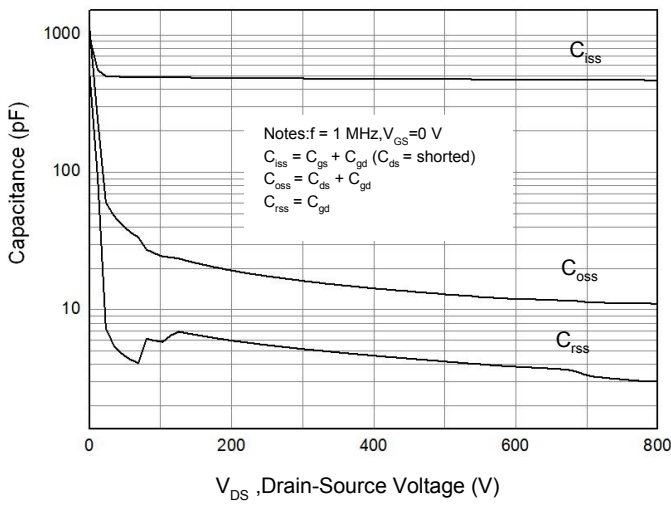


Figure 8. Gate Charge Characteristics

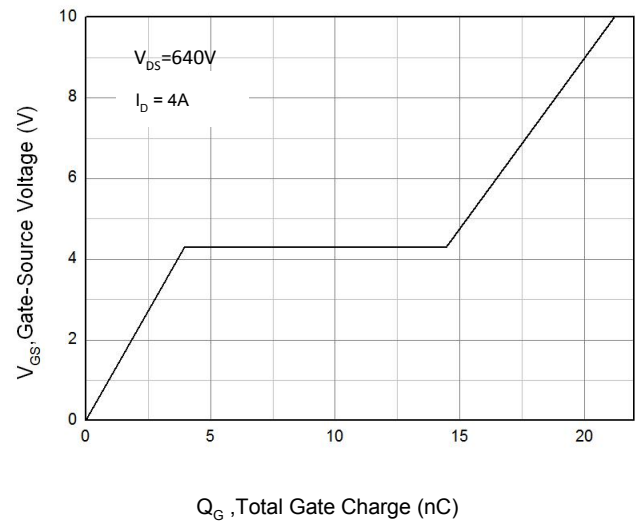


Figure 9. Maximum Safe Operating Area
TO-220F

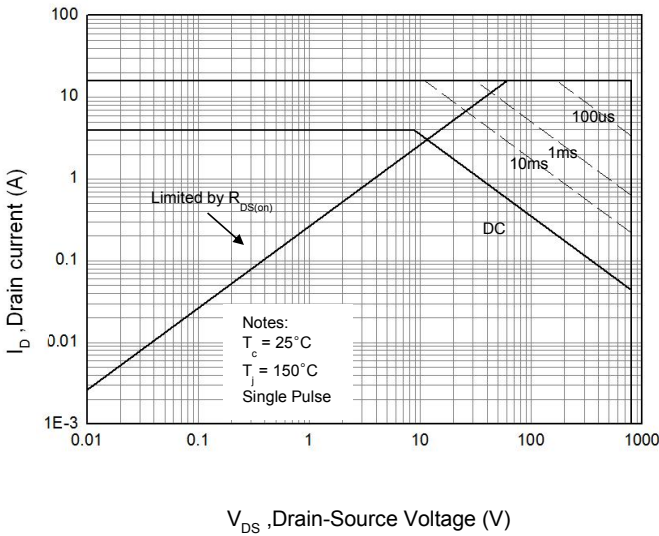


Figure 10. Maximum Safe Operating Area
TO-247/TO-220

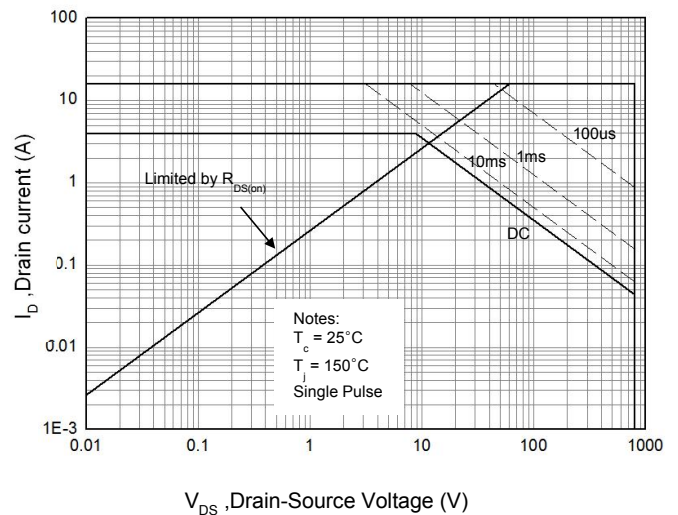


Figure 11. Power Dissipation vs. Temperature
TO-220F

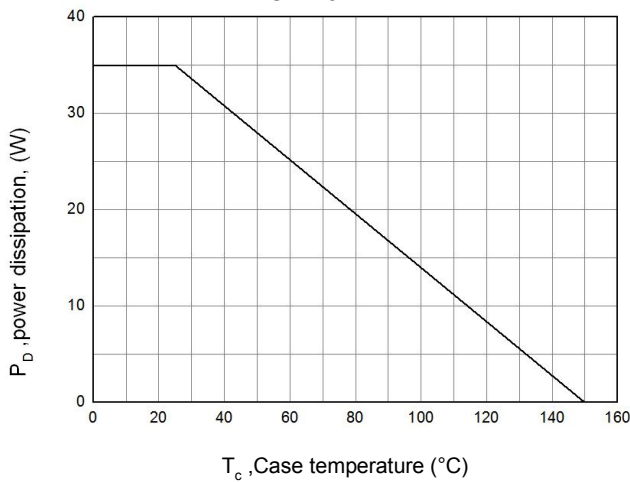


Figure 12. Power Dissipation vs. Temperature
TO-247/TO-220

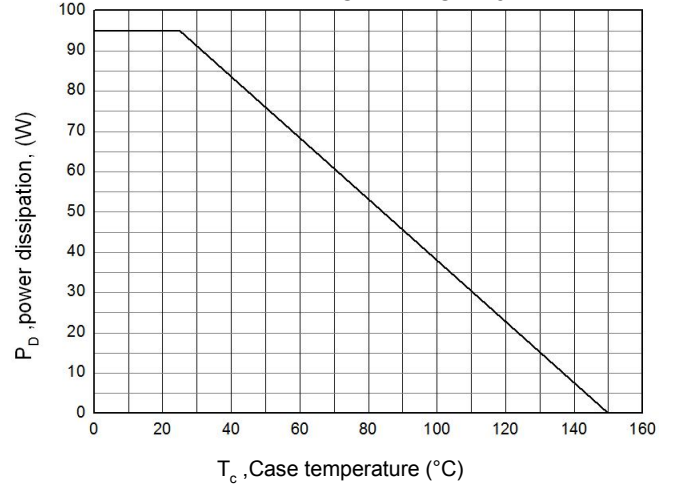


Figure 13. Continuous Drain Current vs. Temperature

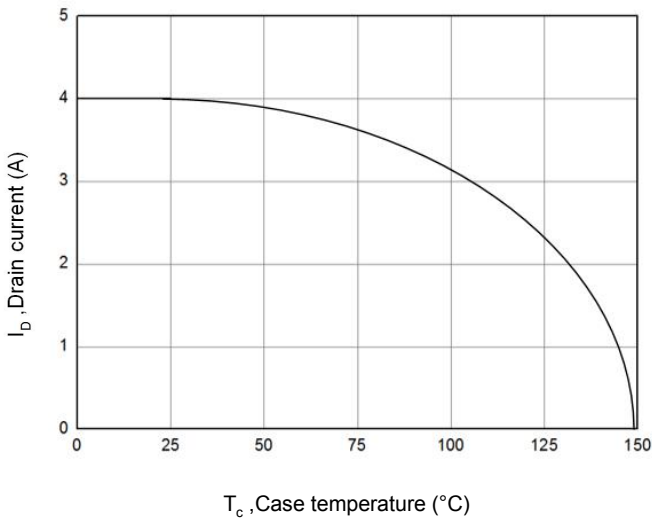


Figure 14. Body Diode Transfer Characteristics

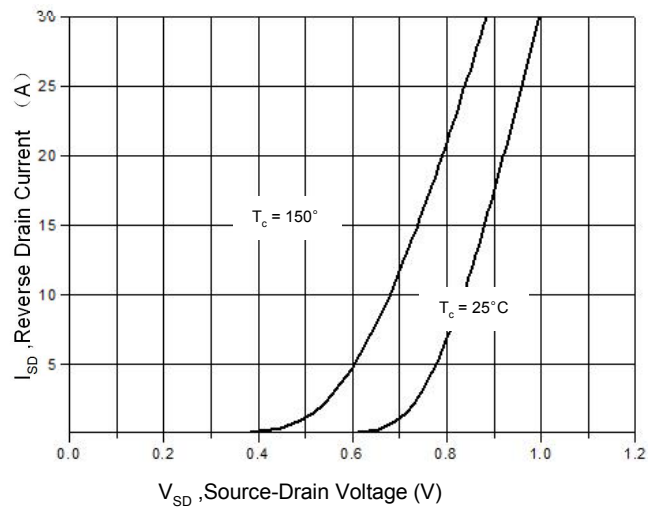


Figure 15 Transient Thermal Impedance, Junction to Case, TO-220F

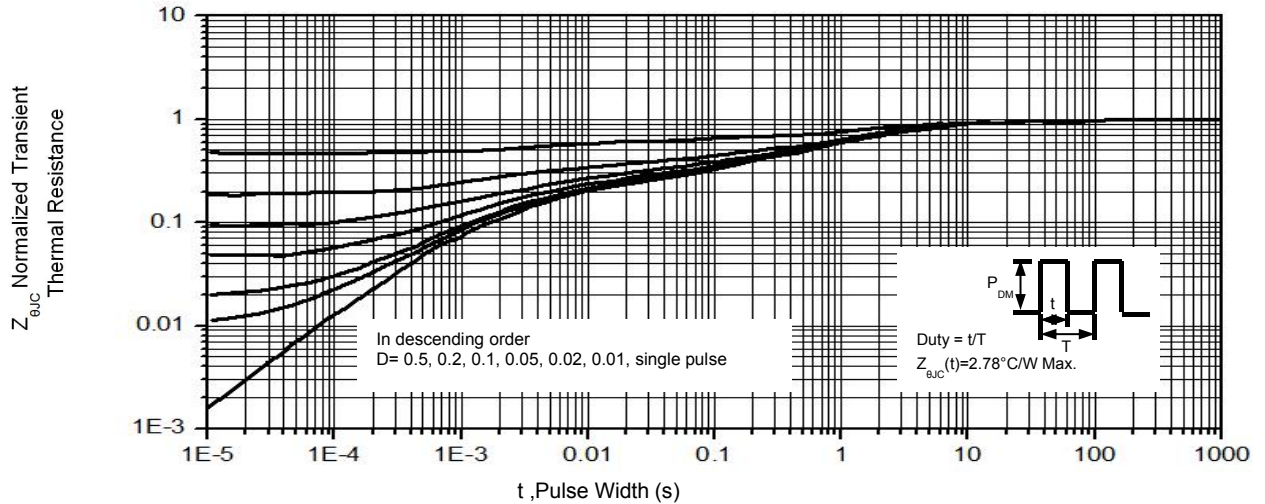
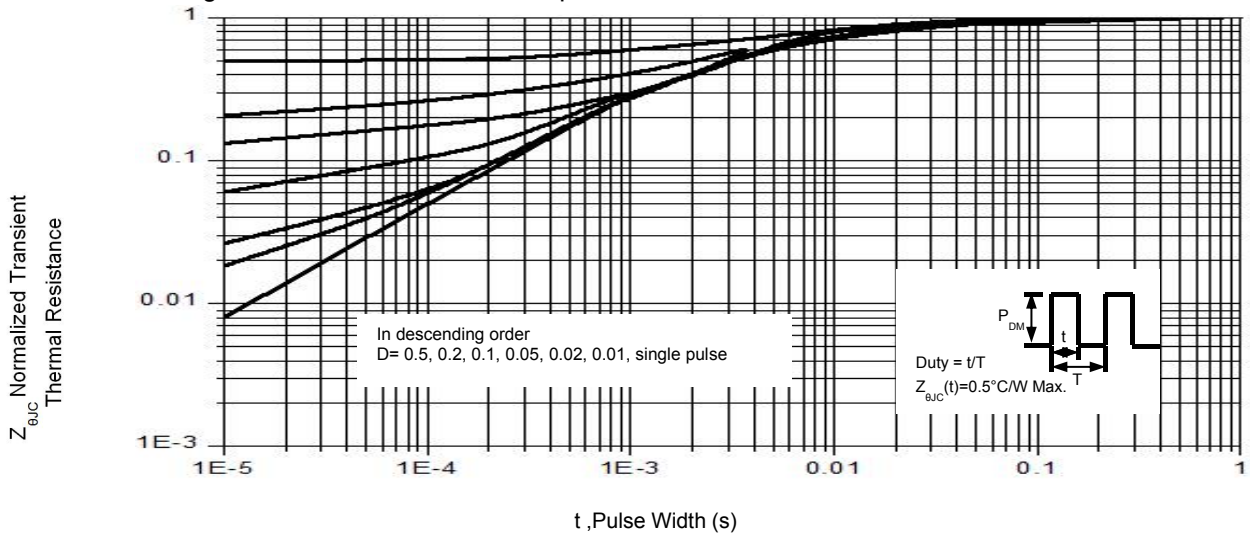
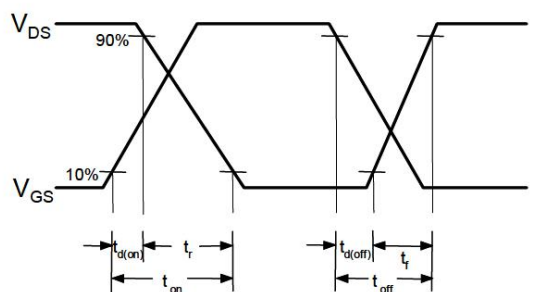
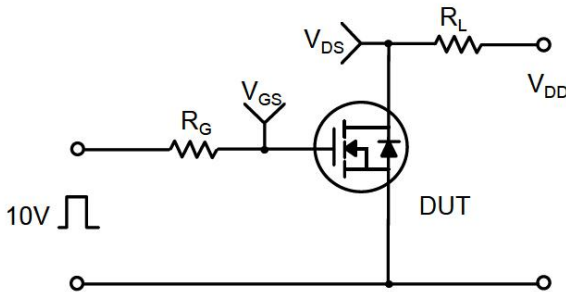
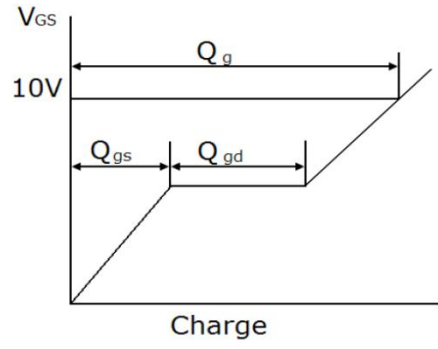


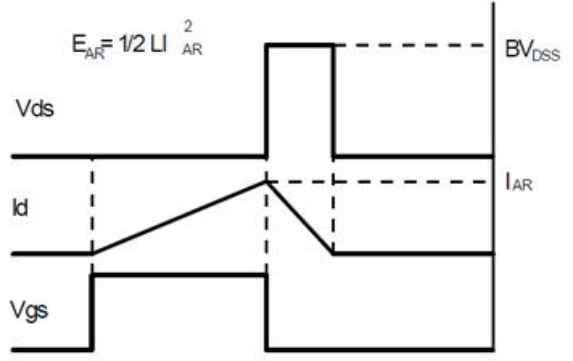
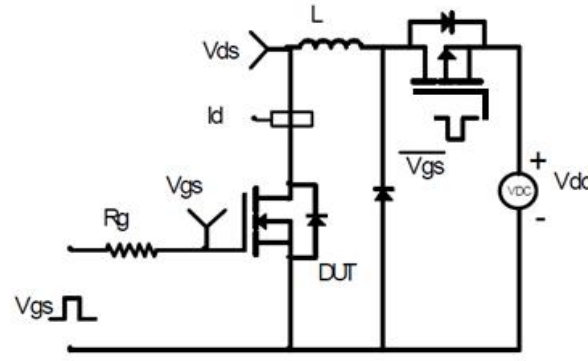
Figure 16. Transient Thermal Impedance, Junction to Case, TO-247/TO-220



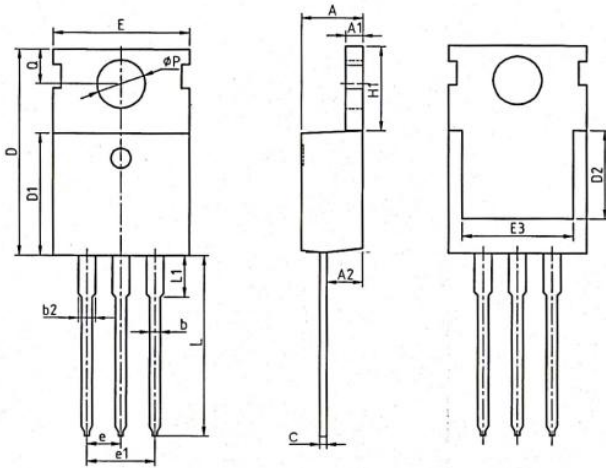
Gate Charge Test Circuit & Waveform



Unclamped Inductive Switching Test Circuit & Waveforms

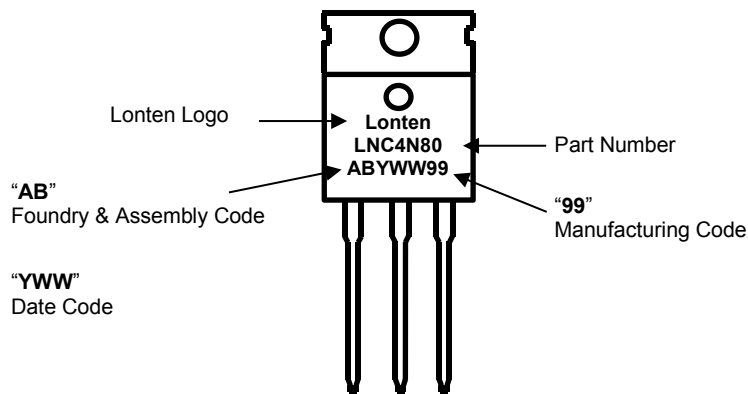


Mechanical Dimensions for TO-220

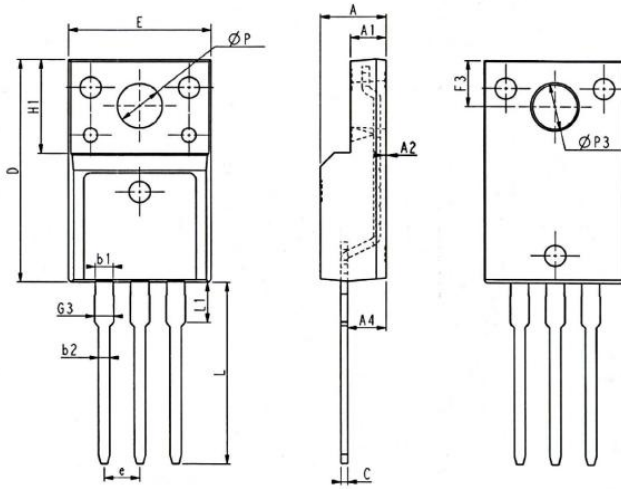


COMMON DIMENSIONS						
SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.37	4.57	4.70	0.172	0.180	0.185
A1	1.25	1.30	1.40	0.049	0.051	0.055
A2	2.20	2.40	2.60	0.087	0.094	0.102
b	0.70	0.80	0.95	0.028	0.031	0.037
b2	1.17	1.27	1.47	0.046	0.050	0.058
c	0.45	0.50	0.60	0.018	0.020	0.024
D	15.10	15.60	16.10	0.594	0.614	0.634
D1	8.80	9.10	9.40	0.346	0.358	0.370
D2	5.50	—	—	0.217	—	—
E	9.70	10.00	10.30	0.382	0.394	0.406
E3	7.00	—	—	0.276	—	—
e	2.54BSC			0.1BSC		
e1	5.08BSC			0.2BSC		
H1	6.25	6.50	6.85	0.246	0.256	0.270
L	12.75	13.50	13.80	0.502	0.531	0.543
L1	—	3.10	3.40	—	0.122	0.134
Øp	3.40	3.60	3.80	0.134	0.142	0.150
Q	2.60	2.80	3.00	0.102	0.110	0.118

TO-220 Part Marking Information

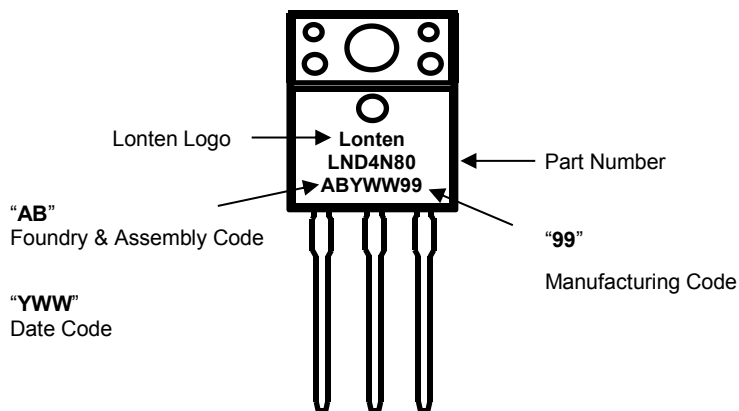


Mechanical Dimensions for TO-220F

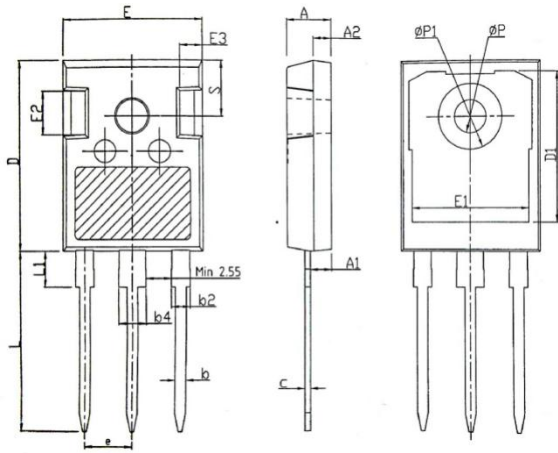


SYMBOL	COMMON DIMENSIONS					
	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
E	9.96	10.16	10.36	0.392	0.400	0.408
A	4.50	4.70	4.90	0.177	0.185	0.193
A1	2.34	2.54	2.74	0.092	0.100	0.108
A2	0.30	0.45	0.60	0.012	0.002	0.024
A4	2.65	2.76	2.96	0.104	0.109	0.117
C	0.40	0.50	0.65	0.016	0.020	0.026
D	15.57	15.87	16.17	0.613	0.625	0.637
H1	6.70REF			0.264REF		
e	2.54BSC			0.1BSC		
ØP	3.03	3.18	3.38	0.119	0.125	0.133
L	12.68	12.98	13.28	0.499	0.511	0.523
L1	2.88	3.03	3.18	0.113	0.119	0.125
ØP3	3.15REF			0.124REF		
F3	3.15	3.30	3.45	0.124	0.130	0.136
G3	1.25	1.35	1.55	0.049	0.053	0.061
b1	1.18	1.28	1.43	0.046	0.050	0.056
b2	0.70	0.80	0.95	0.028	0.031	0.037

TO-220F Part Marking Information

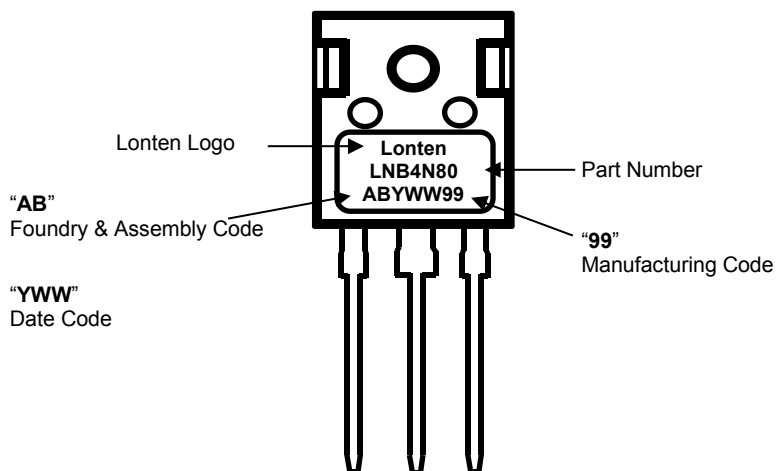


Mechanical Dimensions for TO-247



SYMBOL	mm		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.59
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.80	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	5.44BSC		
L	19.82	19.92	20.22
L1	—	—	4.30
ØP	3.40	3.60	3.80
ØP1	—	—	7.30
S	6.15BSC		

TO-247 Part Marking Information



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